

PATENT

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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)									Applicant: Masayuki KOGA et al.				
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U.S. PATENT DOCUMENTS													
EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
SWL	4	4	6	6	1	7	9	8/84	Kasten				
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FOREIGN PATENT DOCUMENTS													
	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	Translation	
												YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)													
SWL	Kubo et al., "Characteristics of Polycrystalline-Si Thin Film Transistors Fabricated by Excimer Laser Annealing Method", IEEE Transactions on Electron Devices, Oct. 1994, pp. 1876-1879												
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SWL	Kuriyama, "Excimer Laser Crystallization of Silicon Films for AMLCDs", AMLCK Second International Workshop on Active Matrix Liquid Crystal Displays, Sept. 1995, pp. 87-92												
EXAMINER CRANE								DATE CONSIDERED 5/31/02					